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# FGA50S110P 1100 V, 50 A Shorted-anode IGBT

March 2016

#### **Features**

- · Intrinsic Anti-parallel Diode for Soft-switching Applications
- High Switching Frequency Range 10 kHz to 50kHz
- High Temperature Stable Behavior (T<sub>jmax</sub> = 175°C)
- Low Saturation Voltage Drop : VcE(sat) = 2.06 V @ Ic = 50 A
- · Robust Pot Detection Noise Immunity
- · RoHS Compliant (Pb-free lead plating)

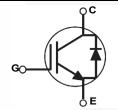
#### **Applications**

- · Induction Cooker, Rice-jar, and Microwave Oven
- · Soft-switching Applications

### **General Description**

Using advanced field stop trench and shorted-anode technology, Fairchild's shorted-anode trench IGBTs offer superior conduction and switching performances for switching applications. This device is tailored to induction cooker and microwave oven.





# **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit	
V <sub>CES</sub>	Collector to Emitter Voltage		1100	V	
$V_{GES}$	Gate to Emitter Voltage		± 25	V	
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	50	A	
10	Collector Current	@ T <sub>C</sub> = 100°C	30	A	
I <sub>CM (1)</sub>	Pulsed Collector Current		120	A	
I <sub>F</sub>	Diode Continuous Forward Current	@ T <sub>C</sub> = 25°C	50	A	
'F	Diode Continuous Forward Current	@ T <sub>C</sub> = 100°C	30	A	
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	300	W	
. 0	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	150	W	
TJ	Operating Junction Temperature		-55 to +175	°C	
T <sub>stg</sub>	Storage Temperature Range		-55 to +175	°C	
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	6	300	°C	

#### Thermal Characteristics

Symbol Parameter		Тур.	Max.	Unit	
R <sub>0JC</sub> (IGBT) Thermal Resistance, Junction to Case, Max		-	0.5	°C/W	
R <sub>0JA</sub> Thermal Resistance, Junction to Ambient, Max		-	40	°C/W	

#### Notes:

1: Limited by T<sub>jmax</sub>

# **Package Marking and Ordering Information**

<b>Device Marking</b>		Device	Package	Reel Size	Tape Width	Quantity	
	FGA50S110P	FGA50S110P	TO-3PN	-	-	30	

# Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = 1100 V, V <sub>GE</sub> = 0 V	-	-	1	mA
I <sub>GES</sub>	G-E Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0 V	-	-	±500	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_C$ = 50 mA, $V_{CE}$ = $V_{GE}$	4.5	5.6	7.5	V
. (* /	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 50 A, V <sub>GE</sub> = 15 V T <sub>C</sub> = 25°C	-	2.06	2.6	V
V <sub>CE(sat)</sub>		I <sub>C</sub> = 50 A, V <sub>GE</sub> = 15 V T <sub>C</sub> = 125°C	-	2.54	-	V
		I <sub>C</sub> = 50 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 175°C	-	2.7	-	V
		$I_F = 50 \text{ A}, T_C = 25^{\circ}\text{C}$	-	1.96	2.6	V
$V_{FM}$	Diode Forward Voltage	I <sub>F</sub> = 50 A, T <sub>C</sub> = 175°C	-	2.67	-	V
Dynamic C	haracteristics		•			
C <sub>ies</sub>	Input Capacitance		-	2056	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1  MHz	-	47.8	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	1 - 1 1/1/12	-	35.8	-	pF
	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	-	-	24	-	ns
t <sub>r</sub>	Rise Time		-	294	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 50 \text{ A},$	-	280	-	ns
t <sub>f</sub>	Fall Time	$R_G = 10 \Omega V_{GE} = 15 V$	-	95	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Resistive Load, T <sub>C</sub> = 25°C	-	2240	-	uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	990	-	uJ
E <sub>ts</sub>	Total Switching Loss		-	3230	-	uJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	24	-	ns
t <sub>r</sub>	Rise Time		-	346	-	ns
$t_{d(off)}$	Turn-Off Delay Time	$V_{CC}$ = 600 V, $I_{C}$ = 50 A, $R_{G}$ = 10 $\Omega$ , $V_{GE}$ = 15 V, Resistive Load,, $T_{C}$ = 175°C	-	308	-	ns
t <sub>f</sub>	Fall Time		-	184	-	ns
E <sub>on</sub>	Turn-On Switching Loss		-	2640	-	uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	1820	-	uJ
E <sub>ts</sub>	Total Switching Loss	1	-	4460	-	uJ
Qg	Total Gate Charge		-	195	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	$V_{CE} = 600 \text{ V}, I_{C} = 50 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	15.4	-	nC
Q <sub>gc</sub>	Gate to Collector Charge		-	99.9	1	nC

**Figure 1. Typical Output Characteristics** 

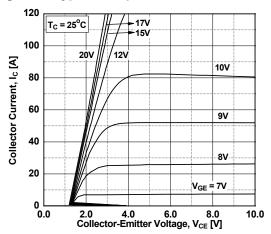


Figure 3. Typical Saturation Voltage Characteristics

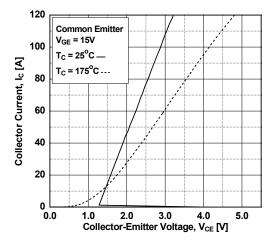


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

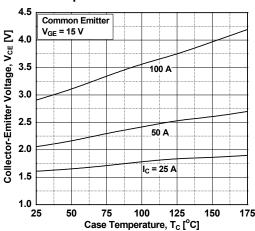
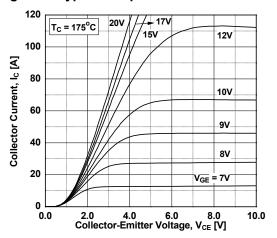


Figure 2. Typical Output Characteristics



**Figure 4. Transfer Characteristics** 

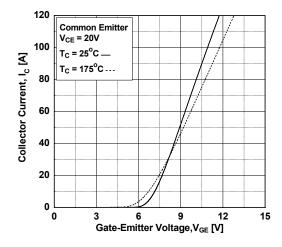


Figure 6. Saturation Voltage vs.  $V_{GE}$ 

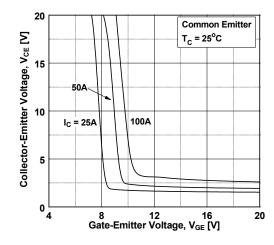


Figure 7. Saturation Voltage vs. V<sub>GE</sub>

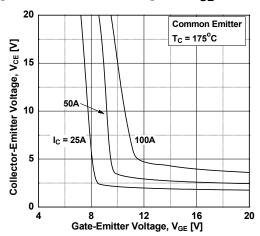


Figure 9. Gate charge Characteristics

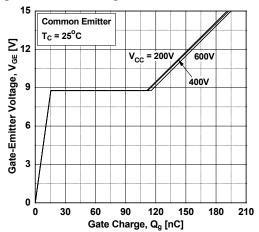
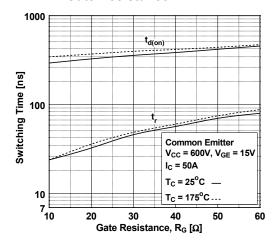


Figure 11. Turn-on Characteristics vs.
Gate Resistance



**Figure 8. Capacitance Characteristics** 

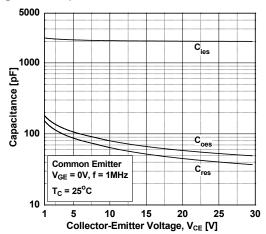


Figure 10. SOA Characteristics

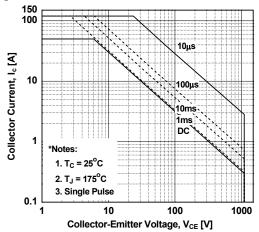


Figure 12. Turn-off Characteristics vs.
Gate Resistance

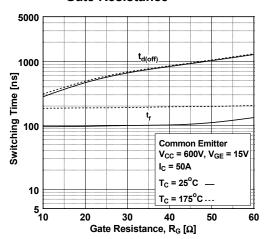
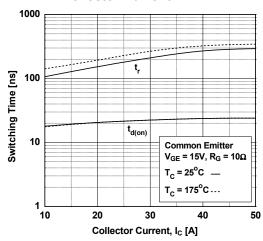


Figure 13. Turn-on Characteristics vs. Collector Current



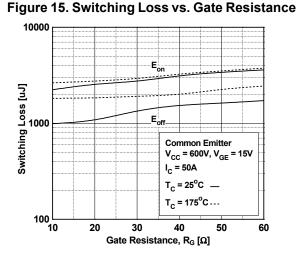


Figure 17. Turn off Switching SOA Characteristics

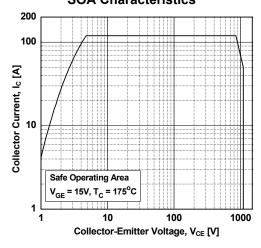


Figure 14. Turn-off Characteristics vs.
Collector Current

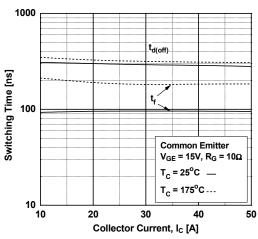


Figure 16. Switching Loss vs. Collector Current

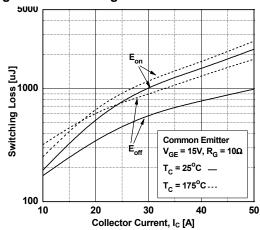


Figure 18. Forward Characteristics

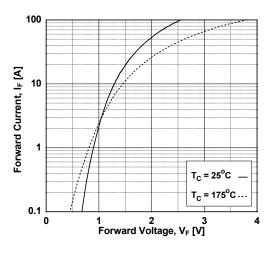
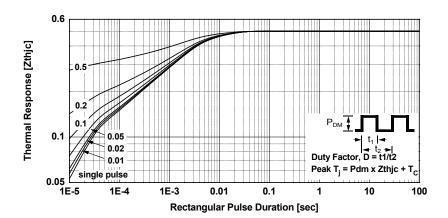
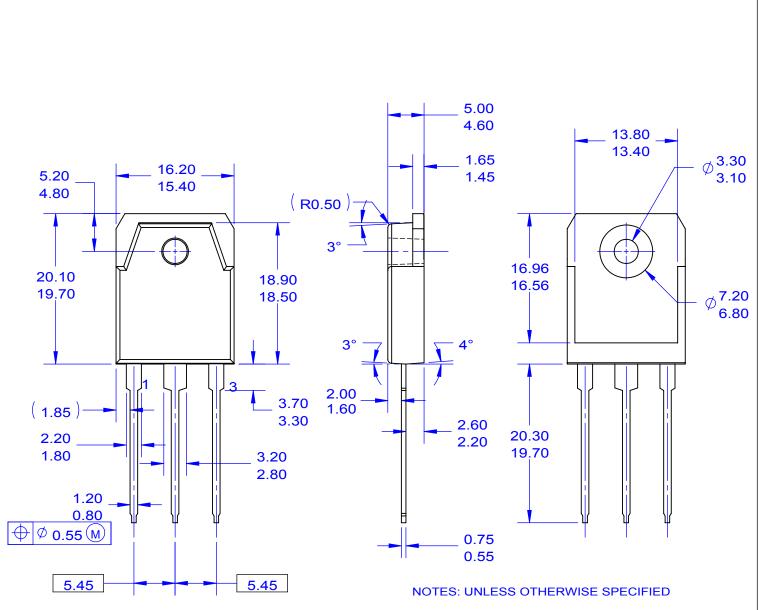
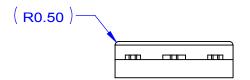


Figure 19. Transient Thermal Impedance of IGBT







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